2SD1030

Silicon NPN epitaxial planar type

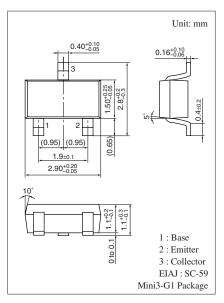
For low-frequency amplification

■ Features

- High forward current transfer ratio hFE
- Low collector-emitter saturation voltage V_{CE(sat)}
- High emitter-base voltage (Collector open) V_{EBO}
- Low noise voltage NV
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	50	V
Collector-emitter voltage (Base open)	V _{CEO}	40	V
Emitter-base voltage (Collector open)	V_{EBO}	15	V
Collector current	I_C	50	mA
Peak collector current	I_{CP}	100	mA
Collector power dissipation	P _C	200	mW
Junction temperature	T_{j}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



Marking symbol: 1Z

■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

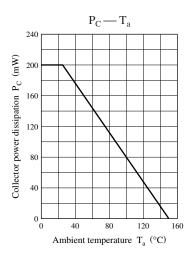
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	40			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \ \mu A, I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 20 \text{ V}, I_{B} = 0$			1	μΑ
Forward current transfer ratio *	h_{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	400		2000	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$		0.05	0.2	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		200		MHz

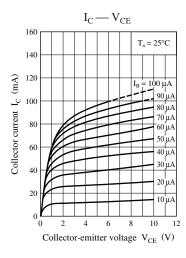
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

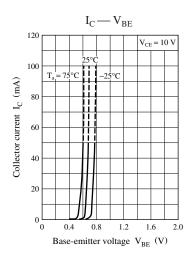
2. *: Rank classification

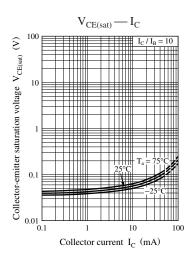
Rank	R	S	Т
h_{FE}	400 to 800	600 to 1 200	1000 to 2000

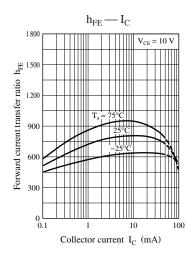
Panasonic

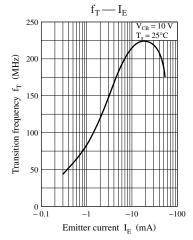


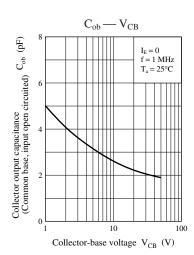












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